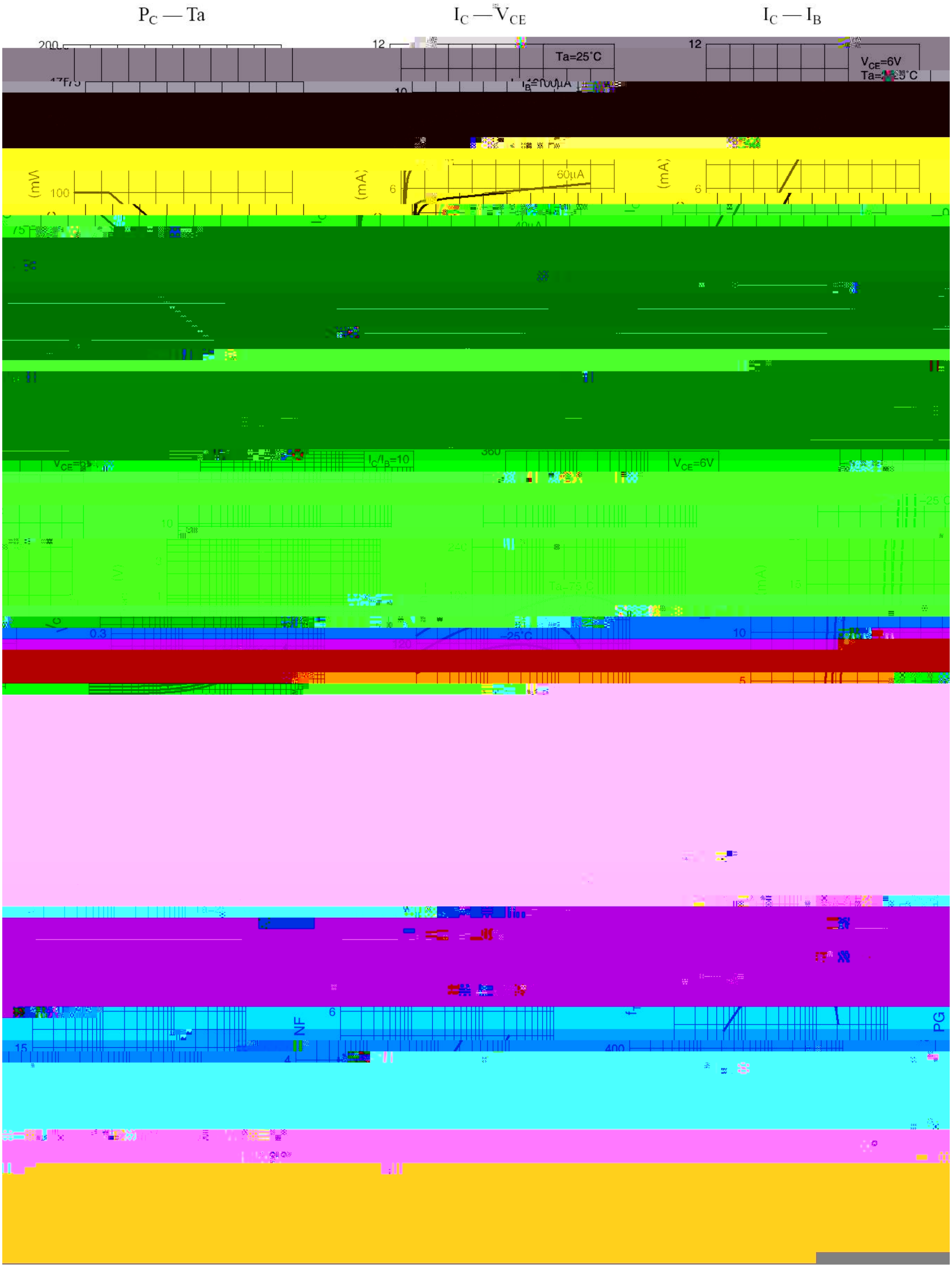
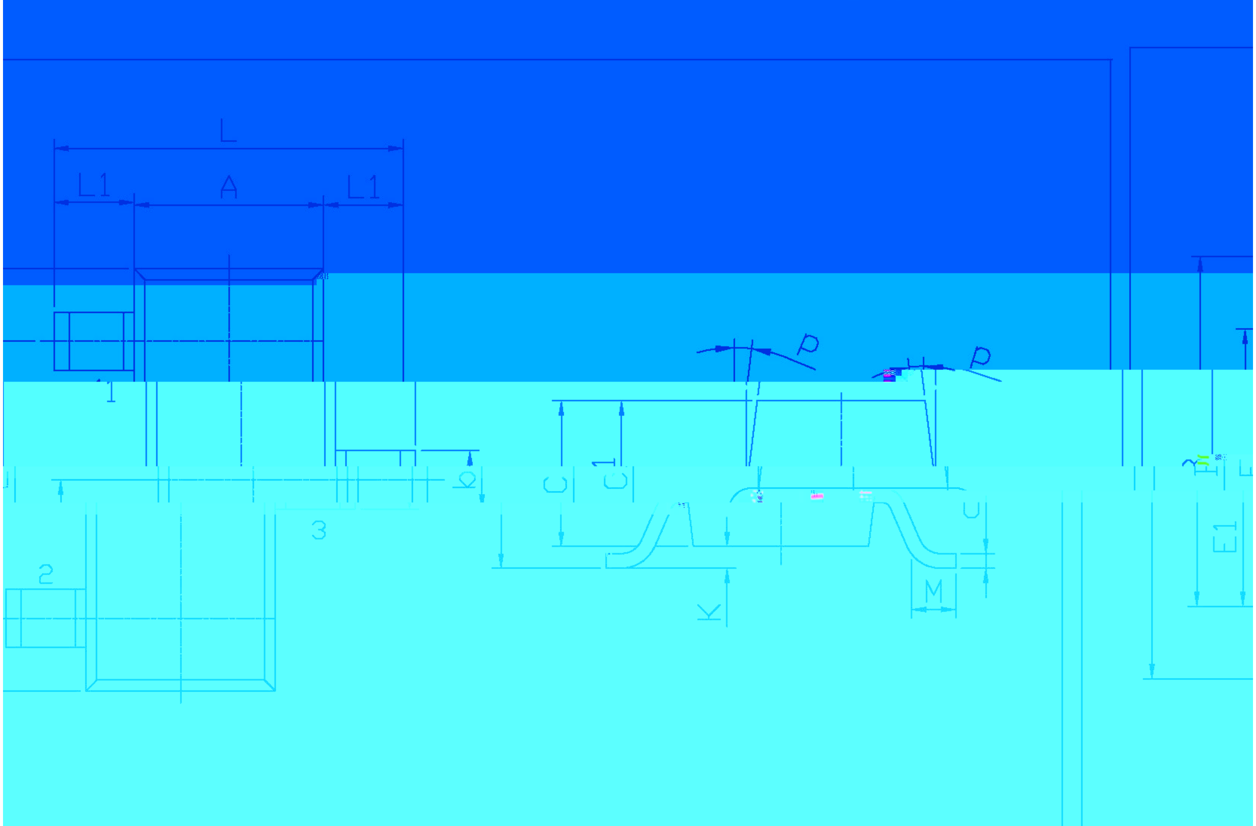
v Ὼ Parameter	ʮ ᴺ Symbol	Ὼ Ӫ Rating	ᴅ Ʉ Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	15	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v Ὼ Parameter	ʮ ᴺ Symbol	╜ ⁏ᶦ ʈ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʓ Ӫ Typ	ῳ ᶾ Ӫ Max	ᴅ Ʉ Unit
Collector- Base Breakdown Voltage	V_{CBO}	I_C=10μA	30			V
Emitter-Base Breakdown Voltage	V_{EBO}	I_E=10μA	3.0			V
DC Current Gain	h_{FE}	V_{CE}=6.0V I_c=1.0mA	40		260	
Transition Frequency	f_T	V_{CB}=6.0V I_c=1.0mA	450	650		MHz
Base to Emitter Voltage	V_{BE}	V_{CB}=6.0V I_c=1.0mA		0.72		V
Common Emitter Reverse Transfer Capacitance	C_{re}	V_{CB}=6.0V I_c=1.0mA f=10.7MHz		0.8	1.0	PF
Power Gain	P_G	V_{CB}=6.0V I_C=1.0mA f=100MHz		24		dB
Noise Figure	NF	V_{CB}=6.0V I_C=1.0mA f=100MHz		3.3		dB


P_C — Ta
I_C — V_{CE}
I_C — I_B
200
175
100
75
(mW)
12
10
6
Ta=25°C
I_B=100μA
60μA
40μA
(mA)
V_{CE}=6V
I_C/I_B=10
360
240
0.3
-25°C
NF
PG
15
400

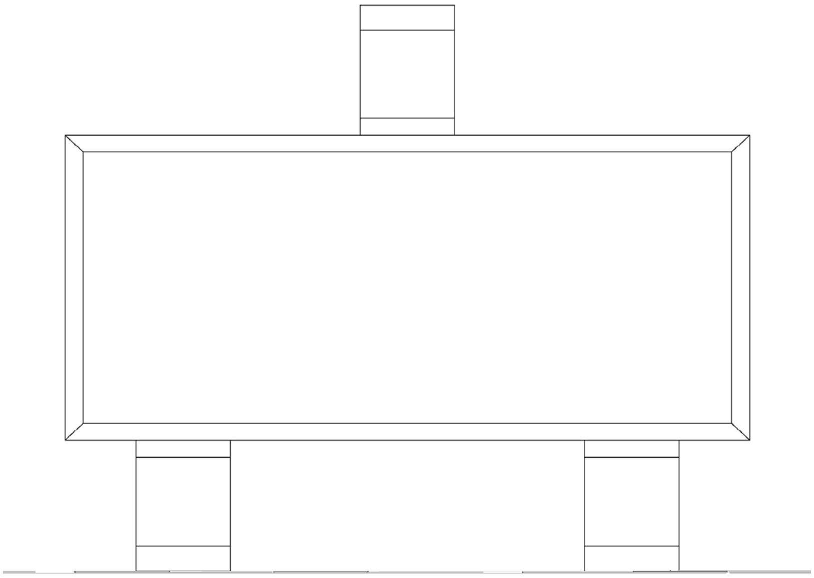
单位：mm



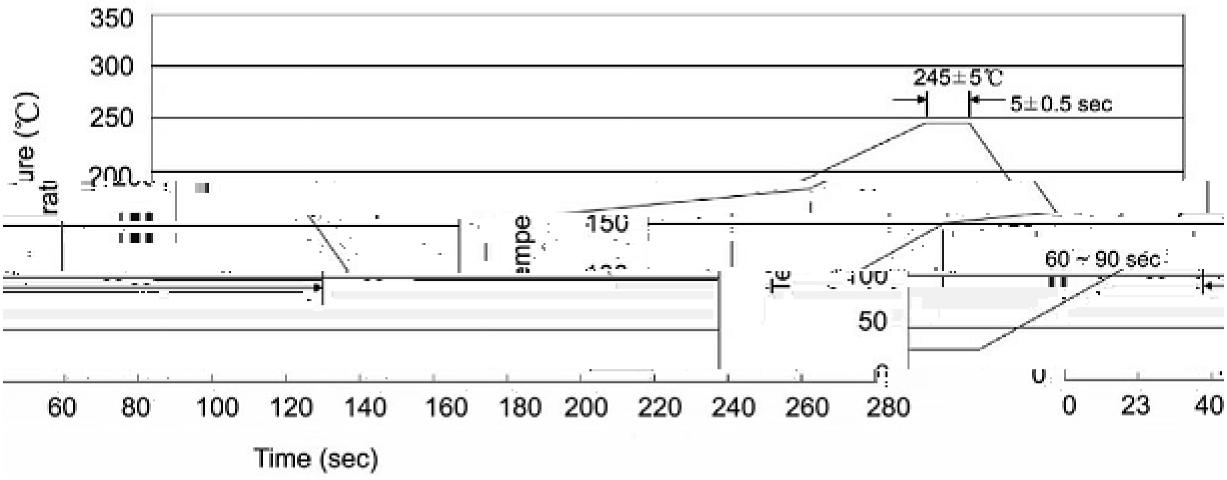
Dimensions In Millimeters

1.70	2.10	M	0.20MIN
0.85	1.05	P	7°
.35	0.55		

E	
E1	
b	



Temperature Profile for IR Reflow Soldering(Pb-Free)



ب ˝ χ

1 ɩ́ ♬ □ ẙ 25 Ḱ 150 ɫ ι ̀H ڑ 60 Ḱ 90sec;

2 Š Ö □ ẙ 245 ° 5 ɫ ι ̀H ڑ ʽY ﾑ ㅒ 5 ° 0.5sec;

3 ì ˙ Ꮑ ˛ ɔ ﻬ ẙ ㅒ 2 Ḱ 10 ɫ /sec.

Note:

1.Preheating:25~150 ɫ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.

3.